

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA817A

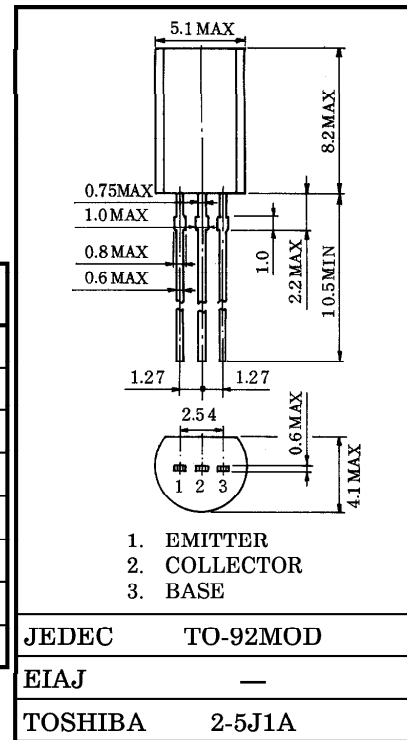
DRIVER STAGE AMPLIFIER APPLICATIONS.
VOLTAGE AMPLIFIER APPLICATIONS.

Unit in mm

- Complementary to 2SC1627A.
- Driver Stage Application of 30 to 35 Watts Amplifiers.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-80	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-400	mA
Emitter Current	I _E	400	mA
Collector Power Dissipation	P _C	800	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Weight : 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = -50V, I _E = 0	—	—	-100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0	—	—	-100	nA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C = -5mA, I _B = 0	-80	—	—	V
DC Current Gain	h _{FE(1)} (Note)	V _{CE} = -2V, I _C = -50mA	70	—	240	
	h _{FE(2)}	V _{CE} = -2V, I _C = -200mA	40	—	—	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -200mA, I _B = -20mA	—	—	-0.4	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -2V, I _C = -5mA	-0.55	—	-0.8	V
Transition Frequency	f _T	V _{CE} = -10V, I _C = -10mA	—	100	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	14	—	pF

Note : h_{FE(1)} Classification O : 70~140, Y : 120~240

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